HAT2045T

Silicon N Channel Power MOS FET High Speed Power Switching

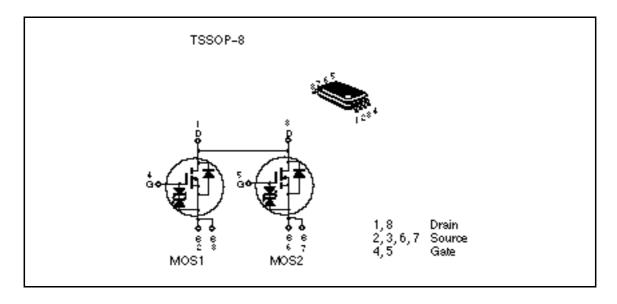
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Target Specification 5th. Edition February 1999

Features

- Low on-resistance
- Capable of 2.5 V gate drive
- · Low drive current
- · High density mounting

Outline





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Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	28	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D	6.0	A
Drain peak current	Note1 D(pulse)	48	A
Body-drain diode reverse drain current	I _{DR}	6.0	A
Channel dissipation	Pch Note2	1.0	W
Channel dissipation	Pch Note3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW 10µs, duty cycle 1 %

- 2. 1 Drive operation; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW 10s
- 3. 2 Drive operation; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW 10s

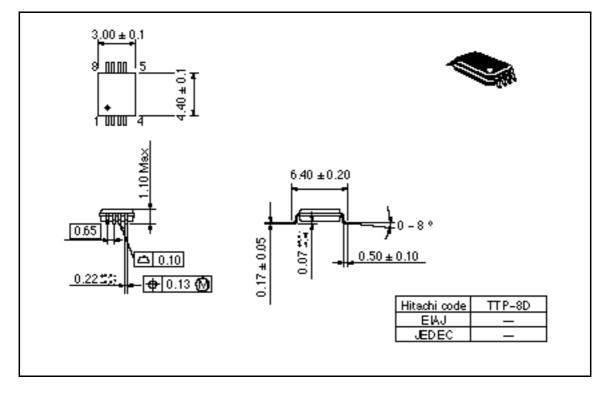
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	28	_	_	V	$I_D = 10$ mA, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±12	_	_	V	$I_{G} = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 28 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 10V$, $I_D = 1mA$
Static drain to source on state	R _{DS(on)}	_	0.020	0.025		$I_D = 3A$, $V_{GS} = 4V^{Note4}$
resistance	R _{DS(on)}	_	0.027	0.037		$I_{\rm D} = 3A, \ V_{\rm GS} = 2.5V^{\rm Note4}$
Forward transfer admittance	y _{fs}	8	13	_	S	$I_{D} = 3A, V_{DS} = 10V^{Note4}$
Input capacitance	Ciss	_	680	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	240	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	170	_	pF	f = 1MHz
Turn-on delay time	t _{d(on)}	_	12	_	ns	$V_{GS} = 4V$, $I_D = 3A$
Rise time	t _r	_	110	_	ns	V _{DD} 10V
Turn-off delay time	$t_{d(off)}$	_	90	_	ns	_
Fall time	t _f	_	100	_	ns	_
Body-drain diode forward voltage	V_{DF}	_	0.85	1.1	V	IF =6.0A, $V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	_	40	_	ns	$IF = 6.0A, V_{GS} = 0$ diF/ dt =20A/µs

Note: 4. Pulse test

Package Dimensions

Unit: mm



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